

2N7002W, 2V7002W

Small Signal MOSFET

60 V, 340 mA, Single, N-Channel, SC-70

Features

- ESD Protected
- Low $R_{DS(on)}$
- Small Footprint Surface Mount Package
- 2V Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Low Side Load Switch
- Level Shift Circuits
- DC-DC Converter
- Portable Applications i.e. DSC, PDA, Cell Phone, etc.

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

| Rating | Symbol | Value | Unit |
|--|----------------|--------------------------|------------------|
| Drain-to-Source Voltage | V_{DSS} | 60 | V |
| Gate-to-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current (Note 1) Steady State | I_D | $T_A = 25^\circ\text{C}$ | 310 |
| | | $T_A = 85^\circ\text{C}$ | 220 |
| $t < 5$ s | | $T_A = 25^\circ\text{C}$ | 340 |
| | | $T_A = 85^\circ\text{C}$ | 240 |
| Power Dissipation (Note 1) Steady State $t < 5$ s | P_D | | 280 |
| | | | 330 |
| Pulsed Drain Current ($t_p = 10 \mu\text{s}$) | I_{DM} | 1.4 | A |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 to +150 | $^\circ\text{C}$ |
| Source Current (Body Diode) | I_S | 250 | mA |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s) | T_L | 260 | $^\circ\text{C}$ |
| Gate-Source ESD Rating (HBM, Method 3015) | ESD | 2000 | V |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|-----------------|-----|--------------------|
| Junction-to-Ambient – Steady State (Note 1) | $R_{\theta JA}$ | 450 | $^\circ\text{C/W}$ |
| Junction-to-Ambient – $t \leq 5$ s (Note 1) | $R_{\theta JA}$ | 375 | |

1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)

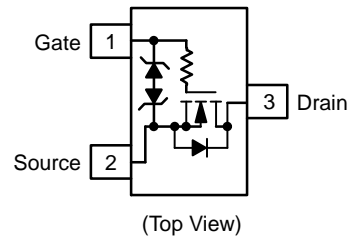


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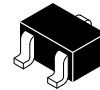
www.onsemi.com

| $V_{(BR)DSS}$ | $R_{DS(on)}$ MAX | I_D MAX (Note 1) |
|---------------|----------------------|-----------------------|
| 60 V | 1.6 Ω @ 10 V | 340 mA |
| | 2.5 Ω @ 4.5 V | |

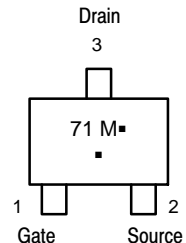
SIMPLIFIED SCHEMATIC



MARKING DIAGRAM & PIN ASSIGNMENT



SC-70/SOT-323
CASE 419
STYLE 8



71 = Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

| Device | Package | Shipping† |
|------------|--------------------|------------------|
| 2N7002WT1G | SC-70 (Pb-Free) | 3000/Tape & Reel |
| 2V7002WT1G | SC-70 (Pb-Free) | 3000/Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Units |
|---|-------------------|--|---------------------------|-----|----------|---------------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-to-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$ | 60 | | | V |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ | | | 71 | | mV/°C |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{GS} = 0\text{ V}, V_{DS} = 60\text{ V}$ | $T_J = 25^\circ\text{C}$ | | 1.0 | μA |
| | | | $T_J = 150^\circ\text{C}$ | | 15 | μA |
| | | $V_{GS} = 0\text{ V}, V_{DS} = 50\text{ V}$ | $T_J = 25^\circ\text{C}$ | | 100 | nA |
| | | | $T_J = 150^\circ\text{C}$ | | 10 | μA |
| Gate-to-Source Leakage Current | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | ± 10 | μA |
| | | $V_{DS} = 0\text{ V}, V_{GS} = \pm 10\text{ V}$ | | | 450 | nA |
| | | $V_{DS} = 0\text{ V}, V_{GS} = \pm 5.0\text{ V}$ | | | 150 | nA |

ON CHARACTERISTICS (Note 2)

| | | | | | | |
|--|------------------|--|-----|------|-----|----------|
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$ | 1.0 | | 2.5 | V |
| Negative Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ | | | 4.0 | | mV/°C |
| Drain-to-Source On Resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 500\text{ mA}$ | | 1.19 | 1.6 | Ω |
| | | $V_{GS} = 4.5\text{ V}, I_D = 200\text{ mA}$ | | 1.33 | 2.5 | |
| Forward Transconductance | g_{FS} | $V_{DS} = 5\text{ V}, I_D = 200\text{ mA}$ | | 530 | | mS |

CHARGES AND CAPACITANCES

| | | | | | | |
|------------------------------|--------------|--|--|------|--|----|
| Input Capacitance | C_{ISS} | $V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 20\text{ V}$ | | 24.5 | | pF |
| Output Capacitance | C_{OSS} | | | 4.2 | | |
| Reverse Transfer Capacitance | C_{RSS} | | | 2.2 | | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS} = 4.5\text{ V}, V_{DS} = 10\text{ V}; I_D = 200\text{ mA}$ | | 0.7 | | nC |
| Threshold Gate Charge | $Q_{G(TH)}$ | | | 0.1 | | |
| Gate-to-Source Charge | Q_{GS} | | | 0.3 | | |
| Gate-to-Drain Charge | Q_{GD} | | | 0.1 | | |

SWITCHING CHARACTERISTICS, $V_{GS} = V$ (Note 3)

| | | | | | | |
|---------------------|--------------|---|--|------|--|----|
| Turn-On Delay Time | $t_{d(ON)}$ | $V_{GS} = 10\text{ V}, V_{DD} = 25\text{ V}, I_D = 500\text{ mA}, R_G = 25\ \Omega$ | | 12.2 | | ns |
| Rise Time | t_r | | | 9.0 | | |
| Turn-Off Delay Time | $t_{d(OFF)}$ | | | 55.8 | | |
| Fall Time | t_f | | | 29 | | |

DRAIN-SOURCE DIODE CHARACTERISTICS

| | | | | | | | |
|-----------------------|----------|--|--------------------------|--|-----|-----|---|
| Forward Diode Voltage | V_{SD} | $V_{GS} = 0\text{ V}, I_S = 200\text{ mA}$ | $T_J = 25^\circ\text{C}$ | | 0.8 | 1.2 | V |
| | | | $T_J = 85^\circ\text{C}$ | | 0.7 | | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$

3. Switching characteristics are independent of operating junction temperatures

TYPICAL CHARACTERISTICS

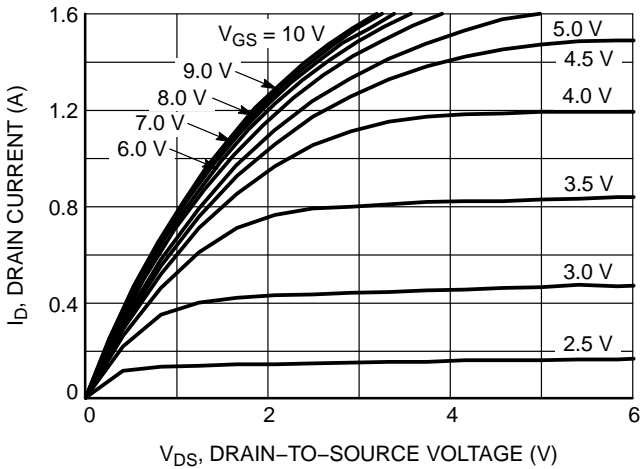


Figure 1. On-Region Characteristics

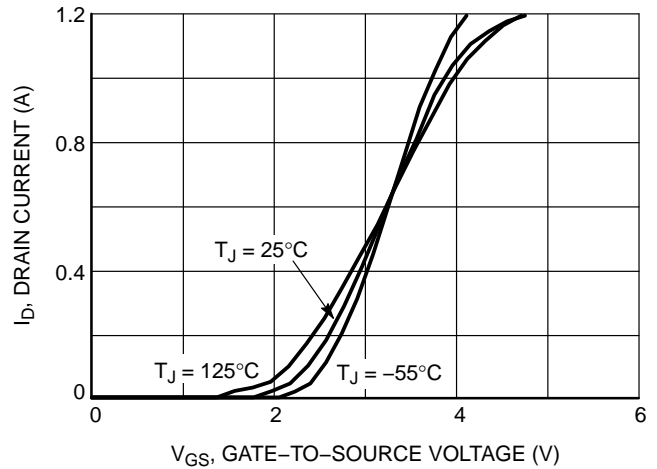


Figure 2. Transfer Characteristics

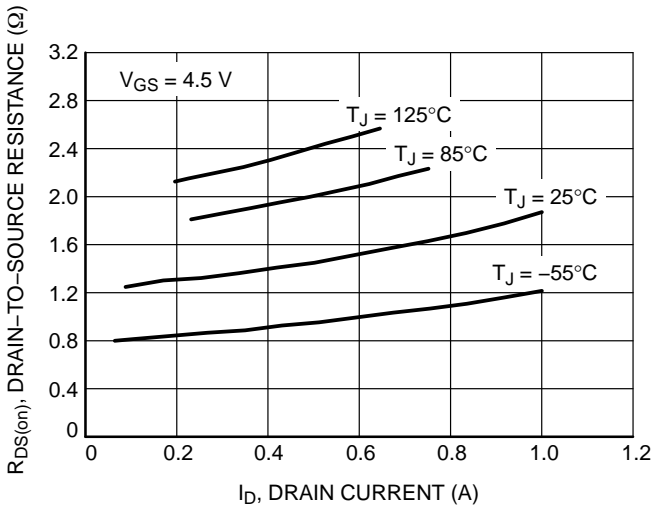


Figure 3. On-Resistance vs. Drain Current and Temperature

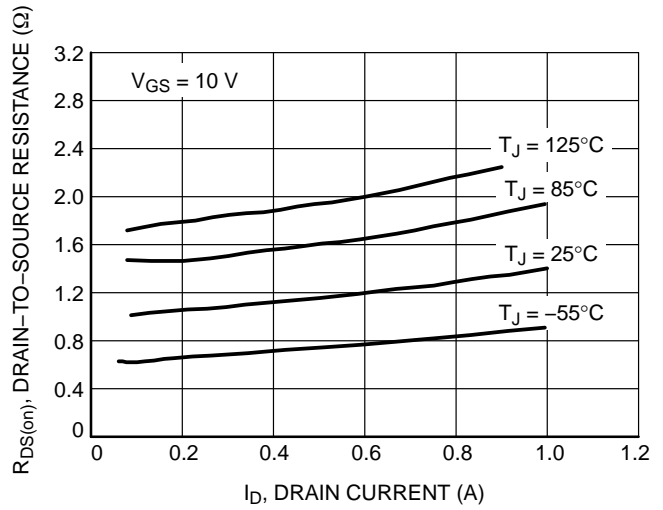


Figure 4. On-Resistance vs. Drain Current and Temperature

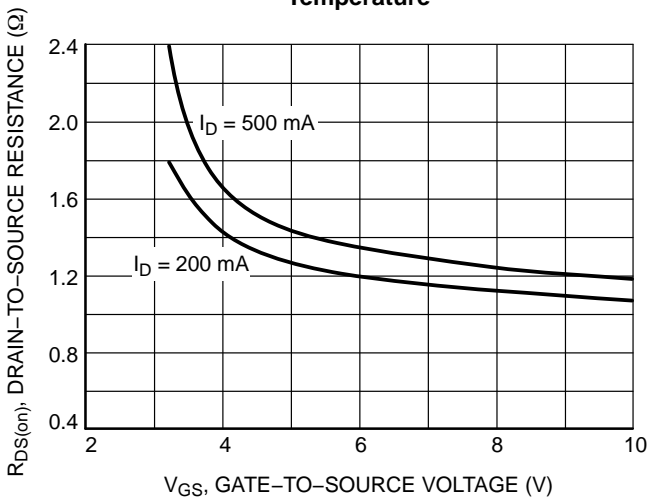


Figure 5. On-Resistance vs. Gate-to-Source Voltage

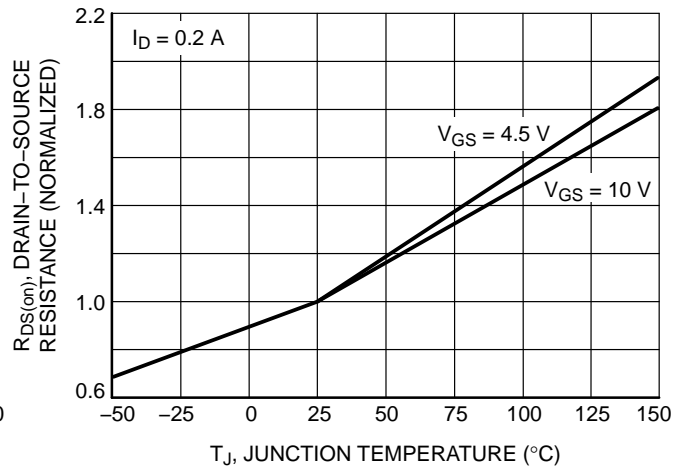


Figure 6. On-Resistance Variation with Temperature

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TYPICAL CHARACTERISTICS

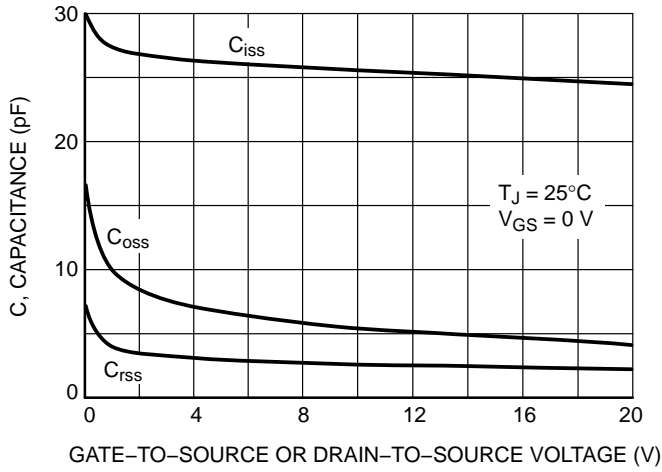


Figure 7. Capacitance Variation

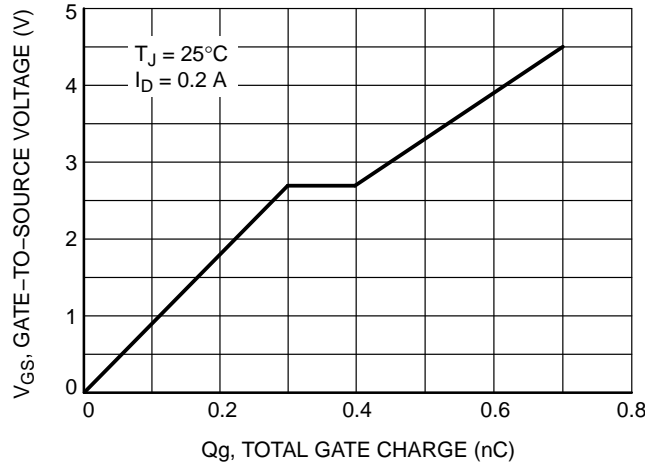


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

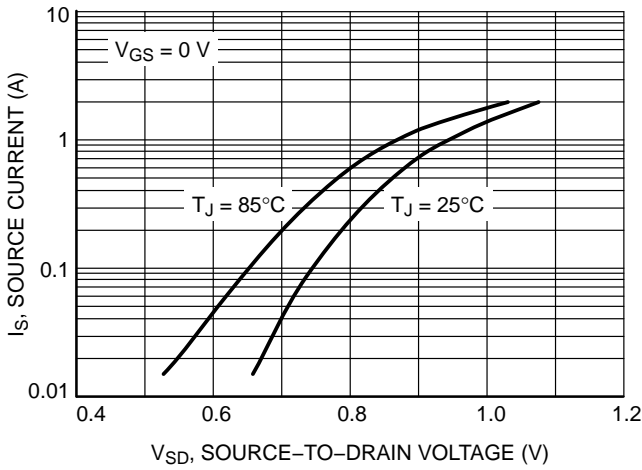


Figure 9. Diode Forward Voltage vs. Current

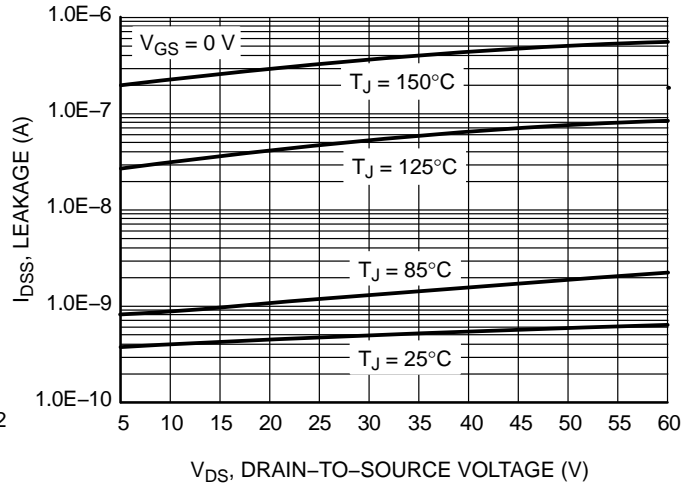


Figure 10. Drain-to-Source Leakage Current vs. Voltage

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



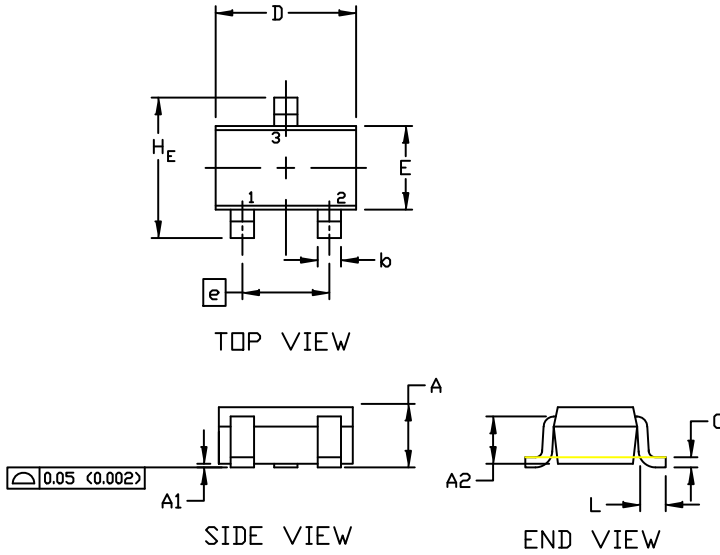
SCALE 4:1

SC-70 (SOT-323)
CASE 419
ISSUE P

DATE 07 OCT 2021

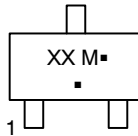
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH



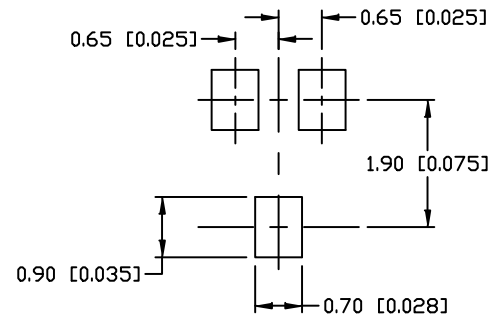
| DIM | MILLIMETERS | | | INCHES | | |
|----------------|-------------|------|------|-----------|-------|-------|
| | MIN. | NDM. | MAX. | MIN. | NDM. | MAX. |
| A | 0.80 | 0.90 | 1.00 | 0.032 | 0.035 | 0.040 |
| A1 | 0.00 | 0.05 | 0.10 | 0.000 | 0.002 | 0.004 |
| A2 | 0.70 REF | | | 0.028 BSC | | |
| b | 0.30 | 0.35 | 0.40 | 0.012 | 0.014 | 0.016 |
| c | 0.10 | 0.18 | 0.25 | 0.004 | 0.007 | 0.010 |
| D | 1.80 | 2.10 | 2.20 | 0.071 | 0.083 | 0.087 |
| E | 1.15 | 1.24 | 1.35 | 0.045 | 0.049 | 0.053 |
| e | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e1 | 0.65 BSC | | | 0.026 BSC | | |
| L | 0.20 | 0.38 | 0.56 | 0.008 | 0.015 | 0.022 |
| H _E | 2.00 | 2.10 | 2.40 | 0.079 | 0.083 | 0.095 |

GENERIC MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the [DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D](#).

SOLDERING FOOTPRINT

- | | | | | | |
|---|---|---|--|---|---|
| STYLE 1: CANCELLED | STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE | STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE | STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE | |
| STYLE 6: PIN 1. EMITTER 2. BASE 3. COLLECTOR | STYLE 7: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 8: PIN 1. GATE 2. SOURCE 3. DRAIN | STYLE 9: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE | STYLE 10: PIN 1. CATHODE 2. ANODE 3. ANODE-CATHODE | STYLE 11: PIN 1. CATHODE 2. CATHODE 3. CATHODE |

| | | |
|------------------|-----------------|--|
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